

Measurement of Mobility-Lifetime products in MAPbI₃ films

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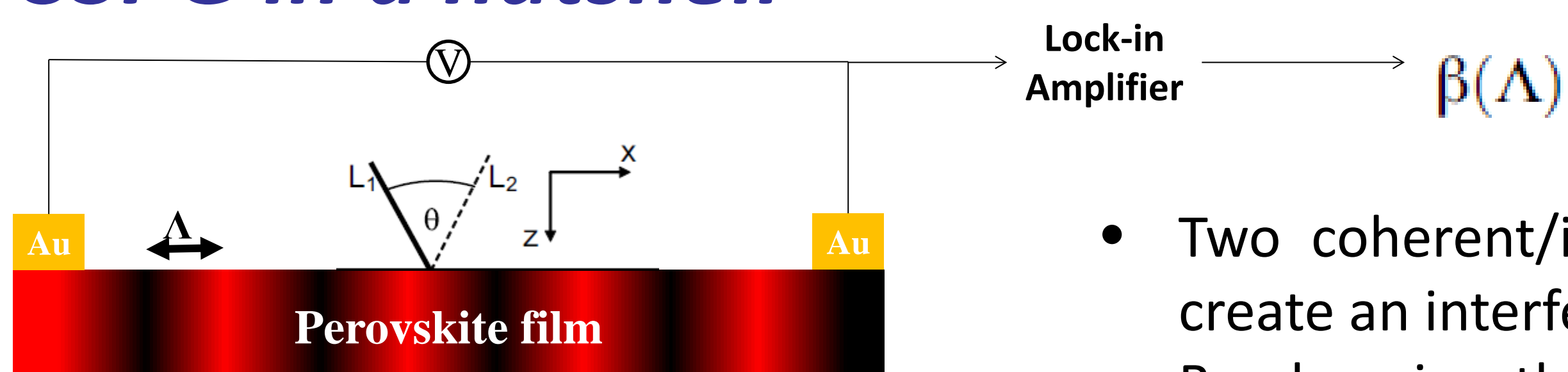
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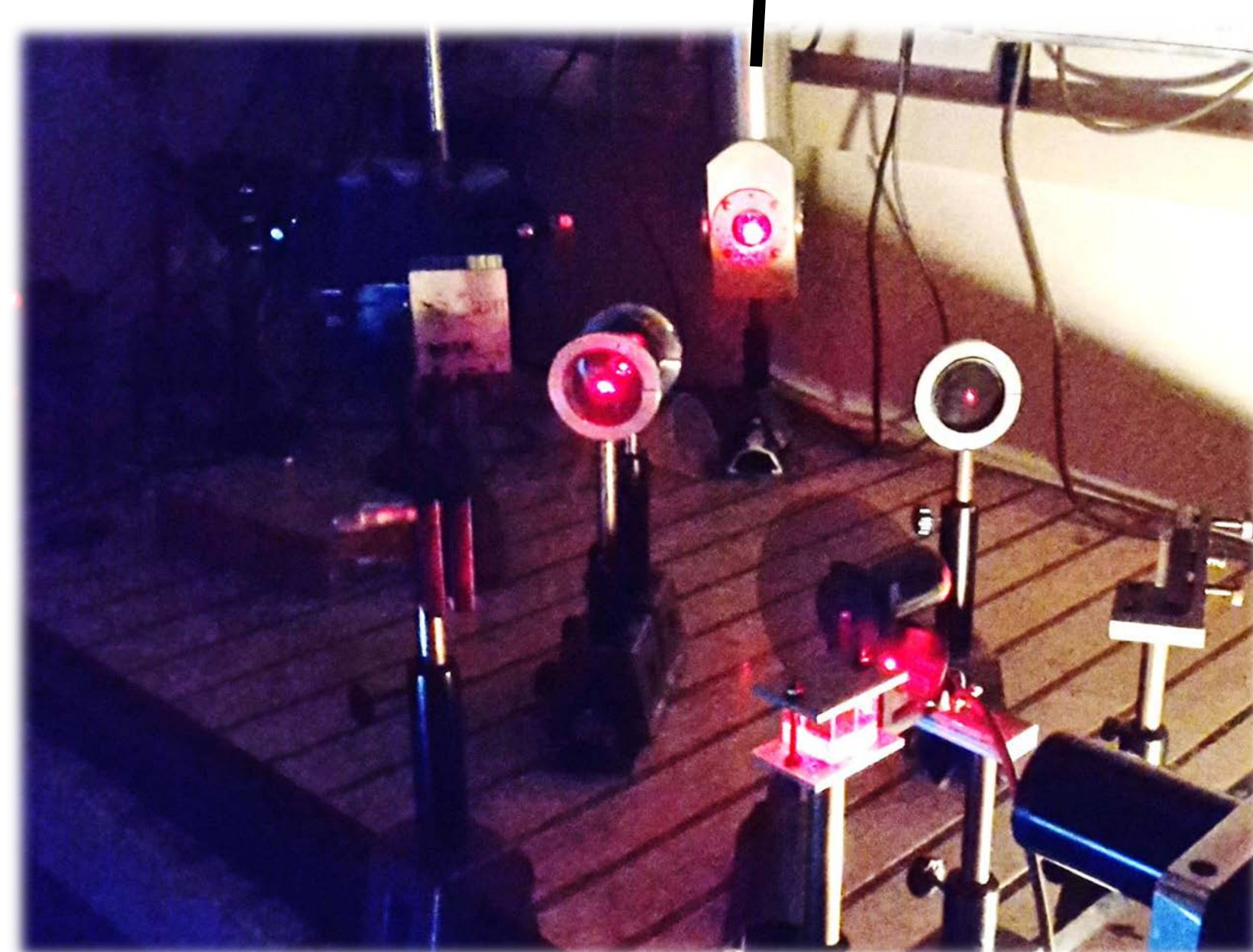
Abstract

In this work we analyze the mobility-lifetime products and their light dependencies in MAPbI₃ films, prepared by the one-step method. Photoconductivity measurements are used to determine the mobility-lifetime product of the majority carriers, while the Steady-State Photocarrier-Grating (SSPG) technique is used to determine the diffusion length and thus the mobility-lifetime product of the minority carriers. SSPG is based on the presence of a spatial sinusoidal modulation in the photogeneration rate G of electronic charge carriers, which induces a so-called photocarrier grating. We find that the obtained ambipolar diffusion lengths of the MAPbI₃ films are highly dependent on the route used for preparing the films. For films prepared using lead acetate we find that the diffusion length is 300-400 nm, without significant dependence on the light intensity used, while for films prepared using lead chloride precursor, the diffusion length is in the range or greater than 700 nm.

SSPG in a nutshell



$$\Lambda = \lambda / [2\sin(\theta/2)]$$

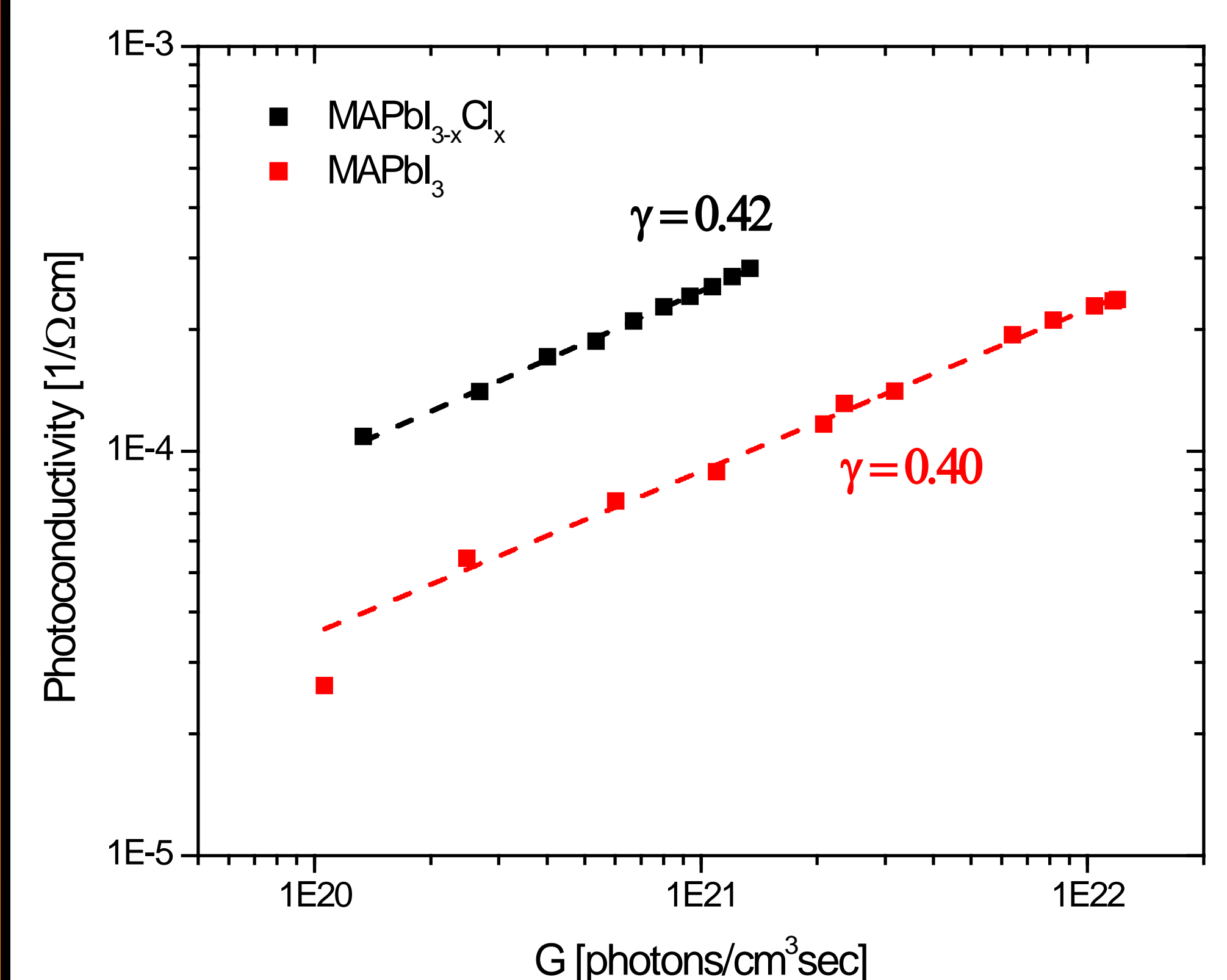


- Two coherent/incoherent laser beams hit the sample and create an interference pattern.
- By changing the polarization of one of the beams, we can measure the photoconductivity with (=coherent) and without (=incoherent) the interference pattern.
- The ratio between the change in photoconductivity in the two conditions is defined as β .
- Measurements using different grating periods, Λ , yield the diffusion length of the minority carriers, L_D , using **Balberg plot**:

$$\sqrt{\frac{2}{1-\beta}} = \frac{1}{\sqrt{Z}} \left(\frac{1}{\Lambda^2} \right) (2\pi L_D)^2 + \frac{1}{\sqrt{Z}} \Rightarrow L_D = \frac{1}{2\pi} \sqrt{\frac{\text{slope}}{\text{intercept}}}$$

Lifetime-Mobility product of the Majority Carriers

$$\sigma_{ph} \propto G^\gamma$$



$$\sigma_{ph} = qG[(\mu\tau)_{maj} + (\mu\tau)_{min}]$$

$$\frac{\sigma_{ph}}{qG} > 1.1 \times 10^{-7} \frac{cm^2}{V}$$

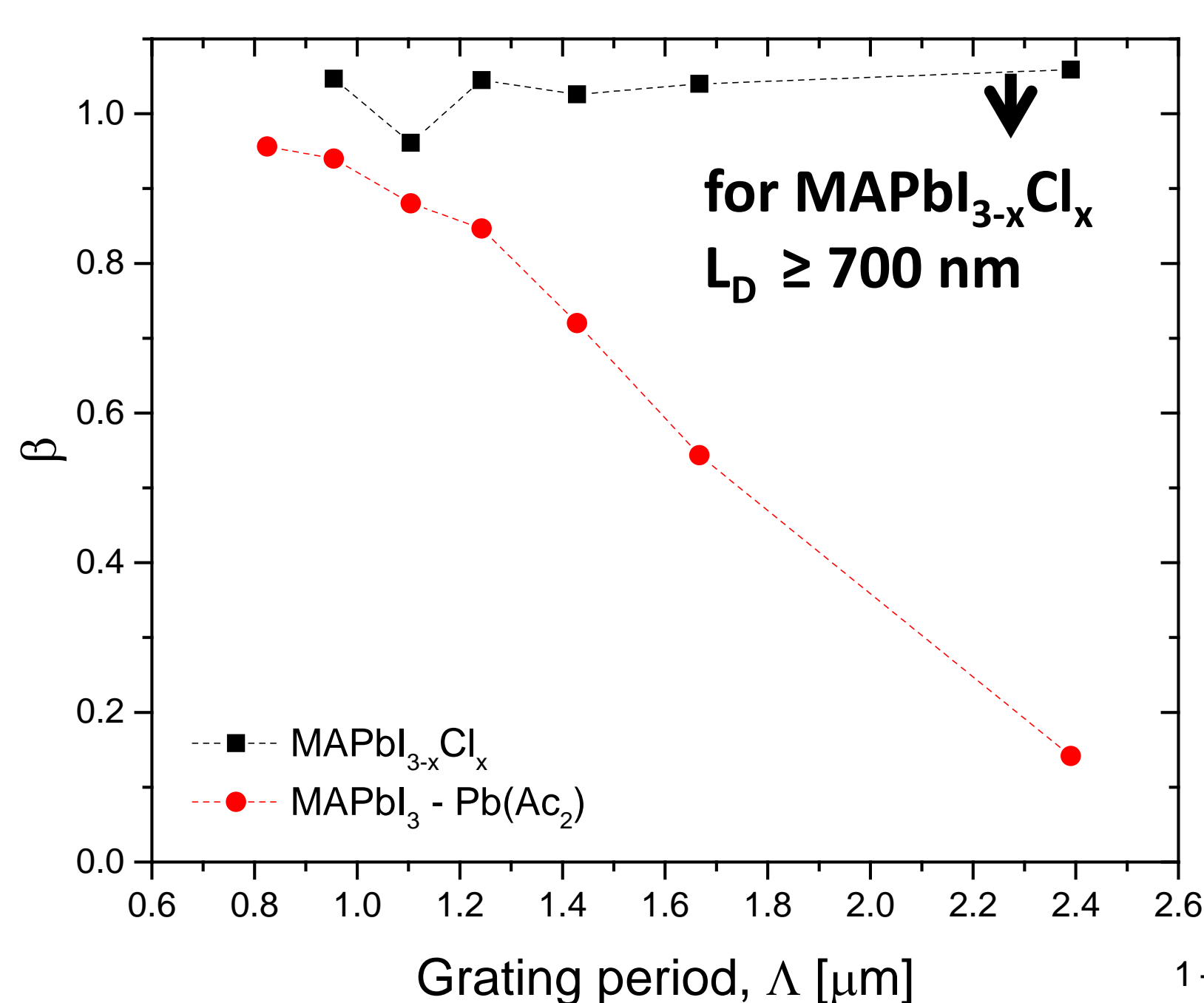
$$\downarrow$$

$$(\mu\tau)_{maj} > 8.1 \times 10^{-8} \frac{cm^2}{V}$$

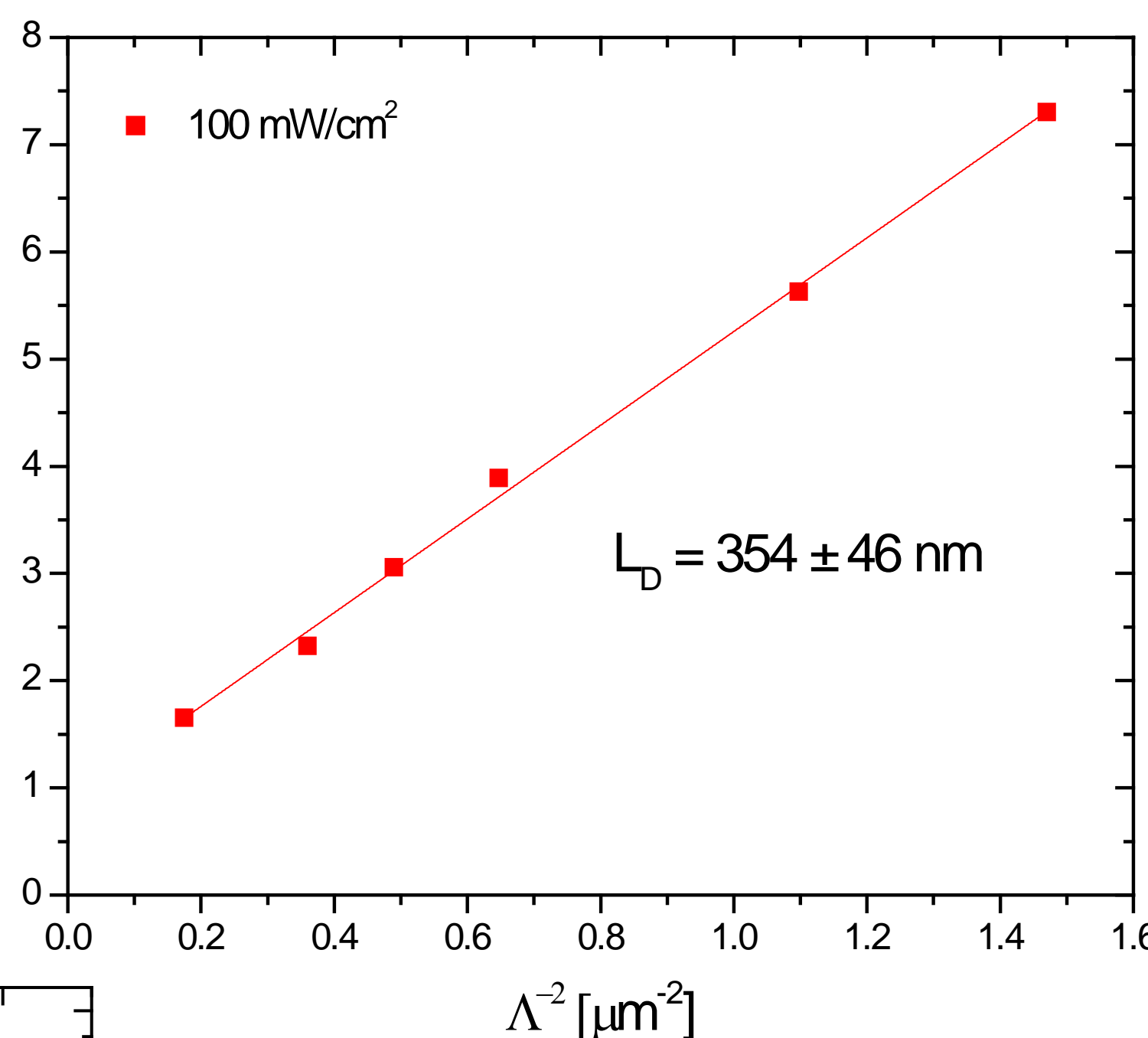
* $(\mu\tau)_{maj}$ will probably be lower due to actual lower G

Mobility-Lifetime product of the Minority Carriers

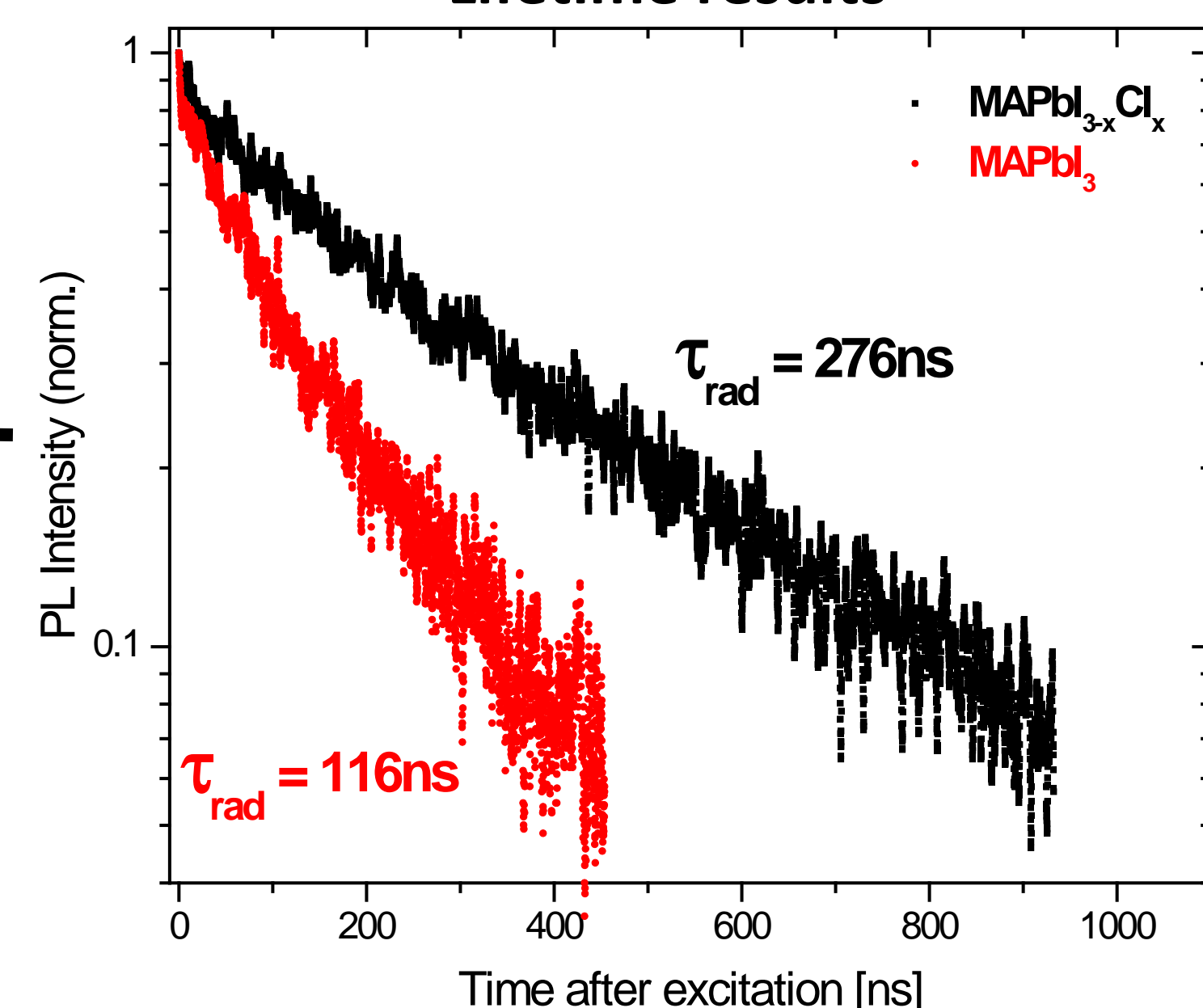
SSPG measurements



Balberg plot For MAPbI₃



Photoluminescence Lifetime results



$$\mu_{min} = 0.25 \pm 0.06 \frac{cm^2}{Vsec}$$

Upper bound for the mobility of the minority carriers!

$$L_D = \sqrt{2 \frac{kT}{e}} (\mu\tau)$$

$$\downarrow$$

$$(\mu\tau)_{min} = 2.9 \times 10^{-8} \frac{cm^2}{V}$$

Conclusions

- By combining Photoconductivity and Diffusion length measurements, we can reliably determine the mobility-lifetime products of the majority and minority charge carriers in MAPbI₃ films and find them to be in the same order of magnitude.
- We find that SSPG can be a reliable method to determine the ambipolar diffusion length of the charge carriers in MAPbI₃ films prepared via different preparation methods and find that for the MAPbI₃, $L_D = 388 \pm 24$ nm, while for the MAPbCl_xI_{3-x} film, $L_D > 700$ nm.
- The upper bound for the mobility of the minority carriers is found to be 0.2-0.3 cm²/Vsec.
- γ is found to be ~ 0.5 , and preliminary results show that L_D is not dependent on the light intensity.
- We can explain our results using the generalized one-recombination level model.

Summary of the results

Material	σ_{dark} [1/Ohm cm]	γ	L_D [nm]	τ_{rad} [ns]	$(\mu\tau)_{min}$ [cm ² /V]	$(\mu\tau)_{maj}$ [cm ² /V]	μ_{min} [cm ² /Vsec]
MAPbI ₃	1.4×10^{-8}	0.42 ± 0.01	388 ± 24	116	2.9×10^{-8}	8.1×10^{-8}	< 0.25
MAPbCl _x I _{3-x}	7.2×10^{-8}	0.40 ± 0.02	≥ 700	276	9.4×10^{-8}	1.4×10^{-7}	< 0.34

Acknowledgements

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